

Amendments to the Claims:

This listing will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A ceramic passive component which comprises
a carrier substrate (1),
at least one first electrode (2) formed of a material selected from the group
consisting of metals and alloys and having a first surface disposed, on the substrate,
at least one thin film dielectric (5) of a thickness in the range of about 0.25-0.75
 μm having a first surface disposed, on a second surface of the at least one first
electrode opposing said first surface of the at least one first electrode, and
at least one second electrode (6) disposed on a second surface of the at least
one dielectric opposing said first surface of the at least one dielectric,
wherein the at least one thin film dielectric (5) comprises a ferroelectric ceramic
material with a voltage-dependent relative dielectric constant ϵ_r , and

wherein the ferroelectric ceramic material with a voltage-dependent dielectric
constant ϵ_r is a material selected from the group consisting of:

$\text{Ba}_{1-x}\text{Sr}_x\text{TiO}_3$ ($0 \leq x \leq 1$), $\text{Pb}_{1-1.5y}\text{La}_y(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ ($0 \leq x \leq 1$, $0 \leq y \leq 0.2$), $\text{Pb}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ ($0 \leq x \leq 1$) doped with Nb, $\text{Pb}_{1-\alpha y}\text{La}_y\text{TiO}_3$ ($0 \leq y \leq 0.3$, $1.3 \leq \alpha \leq 1.5$), $(\text{Pb}, \text{Ca})\text{TiO}_3$, BaTiO_3 with and without dopants, $\text{SrZr}_x\text{Ti}_{1-x}\text{O}_3$ ($0 \leq x \leq 1$) with and without Mn dopants, $\text{BaZr}_x\text{Ti}_{1-x}\text{O}_3$ ($0 \leq x \leq 1$), SrTiO_3 doped with, for example, La, Nb, Fe or Mn,

$(\text{Pb}(\text{Mg}_{1/3}\text{Nb}_{2/3})\text{O}_3)_x - (\text{PbTiO}_3)_{1-x}$ ($0 \leq x \leq 1$)

$(\text{Pb}, \text{Ba}, \text{Sr})(\text{Mg}_{1/3}\text{Nb}_{2/3})_x\text{Ti}_y(\text{Zn}_{1/3}\text{Nb}_{2/3})_{1-x-y}\text{O}_3$ ($0 \leq x \leq 1$, $0 \leq y \leq 1$, $x + y \leq 1$),

$\text{PbNb}_{4/5x}((\text{Zr}_{0.6}\text{Sn}_{0.4})_{1-y}\text{Ti}_y)_{1-x}\text{O}_3$ ($0 \leq x \leq 0.9$, $0 \leq y \leq 1$),

$(\text{Ba}_{1-x}\text{Ca}_x)\text{TiO}_3$ ($0 \leq x \leq 1$),

$(\text{Ba}_{1-x}\text{Sr}_x)\text{TiO}_3$ ($0 \leq x \leq 1$), $(\text{Ba}_{1-x}\text{Pb}_x)\text{TiO}_3$ ($0 \leq x \leq 1$), $(\text{Ba}_{1-x}\text{Sr}_x)(\text{Ti}_{1-x}\text{Zr}_x)\text{O}_3$ ($0 \leq x \leq 1$, $0 \leq y \leq 1$)

(a) $\text{Pb}(\text{Mg}_{1/2}\text{W}_{1/2})\text{O}_3$,

(b) $\text{Pb}(\text{Fe}_{1/2}\text{Nb}_{1/2})\text{O}_3$,

(c) $\text{Pb}(\text{Fe}_{2/3}\text{W}_{1/3})\text{O}_3$,

(d) $\text{Pb}(\text{Ni}_{1/3}\text{Nb}_{2/3})\text{O}_3$,

(e) $\text{Pb}(\text{Zn}_{1/3}\text{Nb}_{2/3})\text{O}_3$

(f) Pb (Sc_{1/2}Ta_{1/2})O₃

as well as combinations of any of the materials (a) to (f) with PbTiO₃ and Pb (Mg_{1/3}Nb_{2/3})O₃ with and without excess lead.

2. (Cancelled)

3. (Previously presented) A ceramic passive component as claimed in claim 1, wherein the at least one first electrode (2) or the at least one second electrode (6) comprise(s) at least a first and a second electrically conducting layer.

4. (Previously presented) A ceramic passive component as claimed in claim 3, wherein the first electrically conducting layer of the at least first electrode(2) or of the at least one second electrode (6) comprises Ti, Cr, Ni_xCr_y (0 ≤ x ≤ 1, 0 ≤ y ≤ 1) or Ti_xW_y (0 ≤ x ≤ 1, 0 ≤ y ≤ 1).

5. (Previously presented) A ceramic passive component as claimed in claim 3, wherein the second electrically conducting layer of the at least one first electrode (2) or of the at least one second electrode (6) comprises a metal or an alloy.

6. (Previously presented) A ceramic passive component as claimed in claim 1, wherein the carrier substrate (1) comprises a ceramic material, a ceramic material with a glass planarization layer, a glass-ceramic material, a glass material, or silicon.

7. (Previously presented) A ceramic passive component as claimed in claim 1, wherein the at least one dielectric (5) comprises multiple layers.

8. (Previously presented) A ceramic passive component as claimed in claim 1, wherein a protective layer (7) is laid over the entire component.

9. (Currently Amended) A voltage-controlled oscillator ~~with as its~~ comprising a capacitive component comprising a ceramic passive component which comprises a carrier substrate (1), at least one first electrode (2) formed of a material selected from the group consisting of metals and alloys and having a first surface disposed on the

substrate, at least one thin film dielectric (5) of a thickness in the range of about 0.25-0.75 μ m having a first surface disposed, on a second surface, opposed to said first surface of the at least first electrode, and at least a second electrode (6) disposed on a second surface of the at least one thin film dielectric, opposed to said first surface of the at least one dielectric, wherein the at least one thin film dielectric (5) comprises a ferroelectric ceramic material with a voltage-dependent relative dielectric constant ϵ_r .

10. (Currently amended) A filter ~~with as its~~ comprising a capacitive component comprising a ceramic passive component which comprises a carrier substrate (1), at least one first electrode (2) formed of a material selected from the group consisting of metals and alloys and having a first surface disposed on the substrate, at least one thin film dielectric (5) of a thickness in the range of about 0.25-0.75 μ m having a first surface disposed on a second surface of the at least one second electrode (6) having a surface disposed on said second surface of the at least one thin film dielectric wherein the at least one thin film dielectric (5) comprises a ferroelectric ceramic material with a voltage-dependent relative dielectric constant ϵ_r .

11. (Currently Amended) A delay line ~~with as its~~ comprising a capacitive component comprising a ceramic passive component which comprises a carrier substrate (1), at least one first electrode formed of a material selected from the group consisting of metal and alloys and (2) having a first surface disposed on the substrate at least one thin film dielectric (5) of a thickness in the range of about 0.25-0.75 μ m having a first surface disposed on a second surface of the one first electrode opposed to said first surface and at least one a second electrode (6) having a surface disposed on said second surface of the at least one thin film dielectric wherein the at least one thin film dielectric (5) comprises a ferroelectric ceramic material with a voltage-dependent relative dielectric constant ϵ_r .

12. (Previously presented) A capacitive ceramic comprising a carrier substrate (1), at least one first electrode (2) formed of a material selected from the group consisting of metals and alloys and having a first surface disposed on the substrate at least one dielectric (5) of a thickness in the range of about 0.25-0.75 μ m with a voltage-dependent

relative dielectric constant ϵ_r having a second surface opposed to said first surface disposed on a second surface of the at least one first electrode opposed to said first surface and at least one second electrode (6) disposed on said second surface of the at least one thin film dielectric as a capacitive component.